

100nm GaN on Si: A Pioneering Technology to Enable High RF Power in Millimeter Wave Bands

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Abstract

OMMIC, major European player in the development of III-V processes, epitaxy and MMIC manufacturing processes continues to improve its portfolio to address new applications of microwave power market space, military and civilian.

In order to expand its offering and offer power solutions for applications from 15 to 94GHz, OMMIC just introduced a process GaN on Si 100nm referred D01GH.

This all new power process has been specifically designed to address the microwave thanks to its 100GHz FT and 180GHz F MAX. The VDD is 15V and the proposed power density of 3.3W / mm is three time higher than the equivalent gate length D01PH GaAs process.